

HIGH-SPEED DIFFERENTIAL LINE DRIVERS

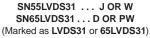
FEATURES

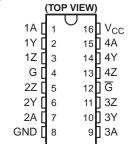
- Meet or Exceed the Requirements of ANSI TIA/EIA-644 Standard
- Low-Voltage Differential Signaling With Typical Output Voltage of 350 mV and 100-Ω Load
- Typical Output Voltage Rise and Fall Times of 500 ps (400 Mbps)
- Typical Propagation Delay Times of 1.7 ns
- Operate From a Single 3.3-V Supply
- Power Dissipation 25 mW Typical Per Driver at 200 MHz
- Driver at High Impedance When Disabled or With V_{CC} = 0
- Bus-Terminal ESD Protection Exceeds 8 kV
- Low-Voltage TTL (LVTTL) Logic Input Levels
- Pin Compatible With AM26LS31, MC3487, and μA9638
- Cold Sparing for Space and High Reliability Applications Requiring Redundancy

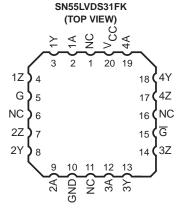
DESCRIPTION

The SN55LVDS31, SN65LVDS31, SN65LVDS3487, and SN65LVDS9638 are differential line drivers that implement the electrical characteristics of low-voltage differential signaling (LVDS). This signaling technique lowers the output voltage levels of 5-V differential standard levels (such as TIA/EIA-422B) to reduce the power, increase the switching speeds, and allow operation with a 3.3-V supply rail. Any of the four current-mode drivers will deliver a minimum differential output voltage magnitude of 247 mV into a 100- Ω load when enabled.

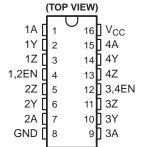
The intended application of these devices and signaling technique is both point-to-point and multidrop (one driver and multiple receivers) data transmission over controlled impedance media of approximately 100 Ω . The transmission media may be printed-circuit board traces, backplanes, or cables. The ultimate rate and distance of data transfer is dependent upon the attenuation characteristics of the media and the noise coupling to the environment.



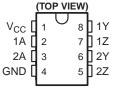




SN65LVDS3487D (Marked as LVDS3487 or 65LVDS3487)



SN65LVDS9638D (Marked as DK638 or LVDS38) SN65LVDS9638DGN (Marked as L38) SN65LVDS9638DGK (Marked as AXG)





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The SN65LVDS31, SN65LVDS3487, and SN65LVDS9638 are characterized for operation from -40°C to 85°C. The SN55LVDS31 is characterized for operation from -55°C to 125°C.

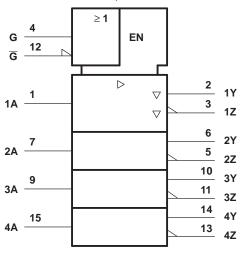
AVAILABLE OPTIONS

T _A (D) SN65LVDS31D SN65LVDS3487D SN65LVDS9638D SN65LVDS9638D	PACKAGE ⁽¹⁾									
T _A	SMALL	OUTLINE	Meon	CHIP CARRIER	CERAMIC DIP	FLAT PACK				
	(D)	(PW)	MSOP	(W)						
	SN65LVDS31D	SN65LVDS31PW	1PW — — — —	_						
40°C to 95°C	SN65LVDS3487D	_	_	_	_	_				
-40 C to 65 C	SN65LVDS9638D	_	SN65LVDS9638DGN	_	_	_				
	_	_	SN65LVDS9638DGK	_	_	_				
–55°C to 125°C	_	_	_	SNJ55LVDS31FK	SNJ55LVDS31J	SNJ55LVDS31W SN55LVDS31W				

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

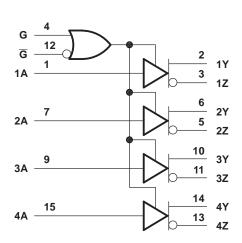
logic symbol†

SN55LVDS31, SN65LVDS31



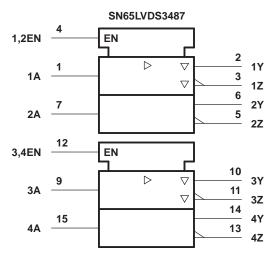
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

'LVDS31 logic diagram (positive logic)



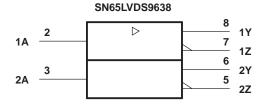


logic symbol†



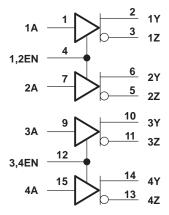
 $^{^\}dagger$ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

SN65LVDS3487 logic diagram (positive logic)



SN65LVDS9638 logic diagram (positive logic)



FUNCTION TABLES

SN55LVDS31, SN65LVDS31⁽¹⁾

INPUT	ENA	BLES	OUTI	PUTS
Α	G	G	Y	Z
Н	Н	Χ	Н	L
L	Н	Χ	L	Н
Н	Х	L	Н	L
L	Х	L	L	Н
X	L	Н	Z	Z
Open	Н	Χ	L	Н
Open Open	X	L	L	Н

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off)

SN65LVDS3487⁽¹⁾

INPUT A	ENABLE EN	OUTPUTS			
INPUT A	ENABLE EN	Y	Z		
Н	Н	Н	L		
L	Н	L	Н		
X	L	Z	Z		
Open	Н	L	Н		

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off)

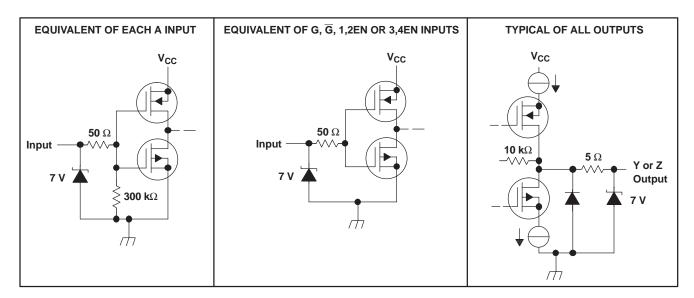
SN65LVDS9638⁽¹⁾

INPUT A	OUT	PUTS
INPUT A	Y	Z
Н	Н	L
L	L	Н
Open	L	Н

(1) H = high level, L = low level



EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		UNIT
V _{CC}	Supply voltage range (2)	−0.5 V to 4 V
VI	Input voltage range	–0.5 V to V _{CC} + 0.5 V
	Continuous total power dissipation	See Dissipation Rating Table
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
T _{stg}	Storage temperature range	–65°C to 150°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ⁽¹⁾ ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D (8)	725 mW	5.8 mW/°C	464 mW	377 mW	_
D (16)	950 mW	7.6 mW/°C	608 mW	494 mW	_
DGK	425 mW	3.4 mW/°C	272 mW	221 mW	_
DGN ⁽²⁾	2.14 W	17.1 mW/°C	1.37 W	1.11 W	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
PW (16)	774 mW	6.2 mW/°C	496 mW	402 mW	_
W	1000 mW	8.0 mW/°C	640 mW	520 mW	200 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

⁽²⁾ All voltages, except differential I/O bus voltages, are with respect to the network ground terminal.

⁽²⁾ The PowerPAD™ must be soldered to a thermal land on the printed-circuit board. See the application note PowerPAD Thermally Enhanced Package (SLMA002).



RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		3	3.3	3.6	V
V_{IH}	High-level input voltage		2			V
V_{IL}	Low-level input voltage				8.0	V
_		SN65 prefix	-40		85	00
IA	Operating free-air temperature	SN55 prefix	-55		125	°C

SN55LVDS31 ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST (CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OD}	Differential output voltage magnitude	$R_L = 100 \Omega$,	See Figure 2	247	340	454	mV
ΔV_{OD}	Change in differential output voltage magnitude between logic states	$R_L = 100 \Omega$,	See Figure 2	-50		50	mV
V _{OC(SS)}	Steady-state common-mode output voltage	See Figure 3		1.125	1.2	1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3		-50		50	mV
V _{OC(PP)}	Peak-to-peak common-mode output voltage	See Figure 3			50	150	mV
		$V_I = 0.8 \text{ V or 2 V},$	Enabled, No load		9	20	
I_{CC}	Supply current	$V_1 = 0.8 \text{ or } 2 \text{ V},$	$R_L = 100 \Omega$, Enabled		25	35	mA
		$V_I = 0$ or V_{CC} ,	Disabled		0.25	1	
I _{IH}	High-level input current	V _{IH} = 2			4	20	μΑ
I _{IL}	Low-level input current	V _{IL} = 0.8 V			0.1	10	μΑ
	Chart aircuit autaut aurrant	$V_{O(Y)}$ or $V_{O(Z)} = 0$			-4	-24	A
I _{OS}	Short-circuit output current	$V_{OD} = 0$				±12	mA
I _{OZ}	High-impedance output current	$V_0 = 0 \text{ or } 2.4 \text{ V}$				±1	μΑ
I _{O(OFF)}	Power-off output current	$V_{CC} = 0$,	V _O = 2.4 V			±4	μΑ
C _i	Input capacitance				3		pF

⁽¹⁾ All typical values are at $T_A = 25$ °C and with $V_{CC} = 3.3$ V.

SN55LVDS31 SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		0.5	1.4	4	ns
t _{PHL}	Propagation delay time, high-to-low-level output		1	1.7	4.5	ns
t _r	Differential output signal rise time (20% to 80%)	$R_L = 100 \Omega, C_L = 10 pF,$	0.4	0.5	1	ns
t _f	Differential output signal fall time (80% to 20%)	See Figure 2	0.4	0.5	1	ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})			0.3	0.6	ns
t _{sk(o)}	Channel-to-channel output skew ⁽²⁾			0.3	0.6	ns
t _{PZH}	Propagation delay time, high-impedance-to-high-level output			5.4	15	ns
t _{PZL}	Propagation delay time, high-impedance-to-low-level output	Coo Figure 4		2.5	15	ns
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output	See Figure 4		8.1	17	ns
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output			7.3	15	ns

⁽¹⁾ All typical values are at $T_A = 25^{\circ}C$ and with $V_{CC} = 3.3 \text{ V}$. (2) $t_{sk(o)}$ is the maximum delay time difference between drivers on the same device.



SN65LVDSxxxx ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETE	R	TEST	CONDITIONS	SN6	65LVDS3 5LVDS34 5LVDS96	87	UNIT
					MIN	TYP ⁽¹⁾	MAX	
V_{OD}	Differential output voltage	ge magnitude	$R_L = 100 \Omega$,	See Figure 2	247	340	454	mV
ΔV_{OD}	Change in differential or magnitude between logi		$R_L = 100 \Omega$,	See Figure 2	-50		50	mV
V _{OC(SS)}	Steady-state common-n	node output voltage	See Figure 3		1.125	1.2	1.37 5	V
ΔV _{OC(S}	Change in steady-state voltage between logic s		See Figure 3		-50		50	mV
V _{OC(PP)}	Peak-to-peak common-	mode output voltage	See Figure 3			50	150	mV
			$V_1 = 0.8 \text{ V or } 2 \text{ V},$	Enabled, No load		9	20	
		SN65LVDS31, SN65LVDS3487	$V_1 = 0.8 \text{ or } 2 \text{ V},$	$R_L = 100 \Omega$, Enabled		25	35	mA
I _{CC}	Supply current	G110021200101	$V_I = 0$ or V_{CC} ,	Disabled		0.25	1	
		SN65LVDS9638	V 0.0.V or 2.V	No load		4.7	8	A
		21402FAD28039	$V_{I} = 0.8 \text{ V or 2 V}$	$R_L = 100 \Omega$		9	13	mA
I _{IH}	High-level input current	<u>.</u>	V _{IH} = 2			4	20	μΑ
I _{IL}	Low-level input current		V _{IL} = 0.8 V			0.1	10	μΑ
	Chart aircuit autaut aurr	n n t	$V_{O(Y)}$ or $V_{O(Z)} = 0$			-4	-24	A
los	Short-circuit output curre	ent	V _{OD} = 0				±12	mA
I _{OZ}	High-impedance output	current	V _O = 0 or 2.4 V				±1	μΑ
I _{O(OFF)}	Power-off output curren	t	$V_{CC} = 0$,	V _O = 2.4 V			±1	μΑ
Ci	Input capacitance					3		pF

⁽¹⁾ All typical values are at $T_A = 25$ °C and with $V_{CC} = 3.3$ V.

SN65LVDSxxxx SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	Propagation delay time, high-impedance-to-low-level output Propagation delay time, high-level-to-high-impedance output	TEST CONDITIONS	SI SN SN	UNIT		
			MIN	TYP ⁽¹⁾	MAX	
t _{PLH}	Propagation delay time, low-to-high-level output		0.5	1.4	2	ns
t _{PHL}	Propagation delay time, high-to-low-level output		1	1.7	2.5	ns
t _r	Differential output signal rise time (20% to 80%)	$R_L = 100 \Omega, C_L = 10 pF,$	0.4	0.5	0.6	ns
t _f	Differential output signal fall time (80% to 20%)	See Figure 2	0.4	0.5	0.6	ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})			0.3	0.6	ns
t _{sk(o)}	Channel-to-channel output skew ⁽²⁾			0	0.3	ns
t _{sk(pp)}	Part-to-part skew ⁽³⁾				800	ps
t _{PZH}	Propagation delay time, high-impedance-to-high-level output			5.4	15	ns
t _{PZL}	Propagation delay time, high-impedance-to-low-level output	Soo Figure 4		2.5	15	ns
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output	See Figure 4		8.1	15	ns
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output			7.3	15	ns

⁽¹⁾ All typical values are at $T_A = 25^{\circ}C$ and with $V_{CC} = 3.3 \text{ V}$.

⁽²⁾ t_{sk(0)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

⁽³⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, same temperature, and have identical packages and test circuits.



PARAMETER MEASUREMENT INFORMATION

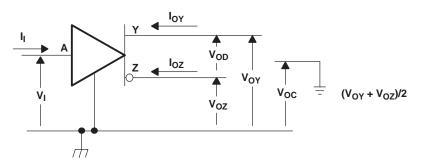
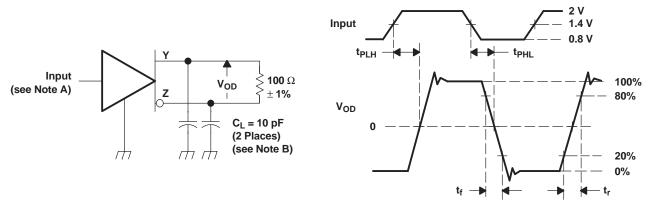
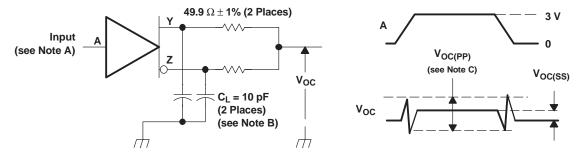


Figure 1. Voltage and Current Definitions



- NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, pulse repetition rate (PRR) = 50 Mpps, pulse width = 10 ± 0.2 ns.
 - B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.

Figure 2. Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal

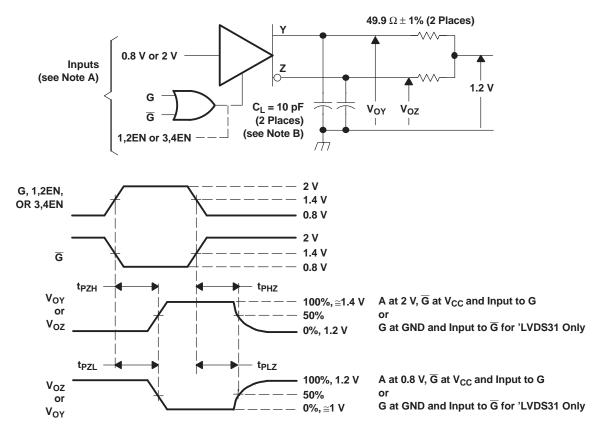


- NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, pulse repetition rate (PRR) = 50 Mpps, pulse width = 10 ± 0.2 ns.
 - B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.
 - C. The measurement of V_{OC(PP)} is made on test equipment with a -3-dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage



PARAMETER MEASUREMENT INFORMATION (continued)



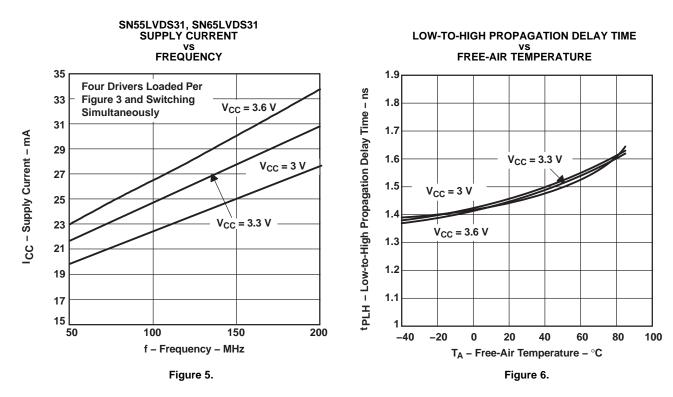
NOTES: A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f < 1$ ns, pulse repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns.

B. C_L includes instrumentation and fixture capacitance within 6 mm of the D.U.T.

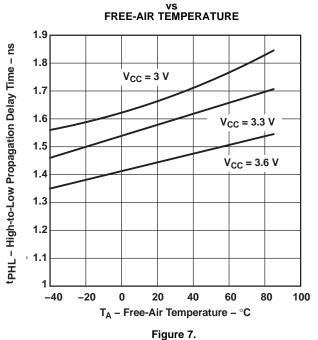
Figure 4. Enable-/Disable-Time Circuit and Definitions



TYPICAL CHARACTERISTICS



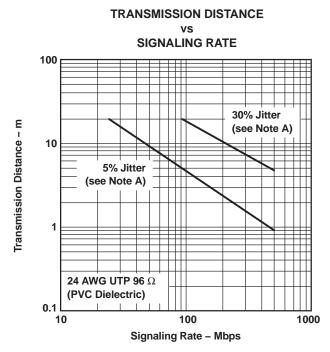
HIGH-TO-LOW PROPAGATION DELAY TIME





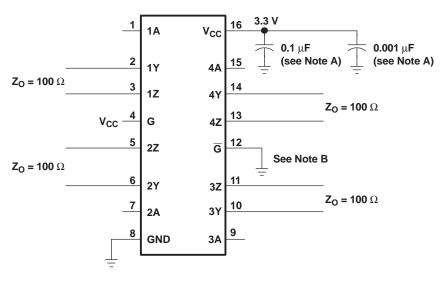
APPLICATION INFORMATION

The devices are generally used as building blocks for high-speed point-to-point data transmission where ground differences are less than 1 V. Devices can interoperate with RS-422, PECL, and IEEE-P1596. Drivers/receivers approach ECL speeds without the power and dual supply requirements.



A. This parameter is the percentage of distortion of the unit interval (UI) with a pseudorandom data pattern.

Figure 8. Typical Transmission Distance Versus Signaling Rate

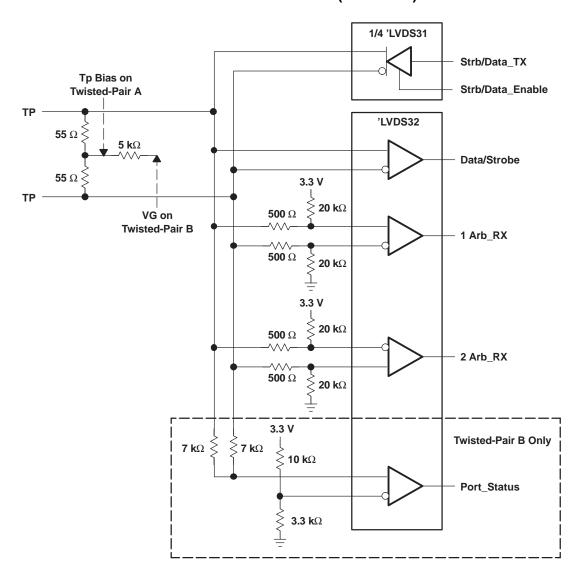


- NOTES: A. Place a $0.1-\mu F$ and a $0.001-\mu F$ Z5U ceramic, mica, or polystyrene dielectric, 0805 size, chip capacitor between V_{CC} and the ground plane. The capacitors should be located as close as possible to the device terminals.
 - B. Unused enable inputs should be tied to V_{CC} or GND, as appropriate.

Figure 9. Typical Application Circuit Schematic



APPLICATION INFORMATION (continued)



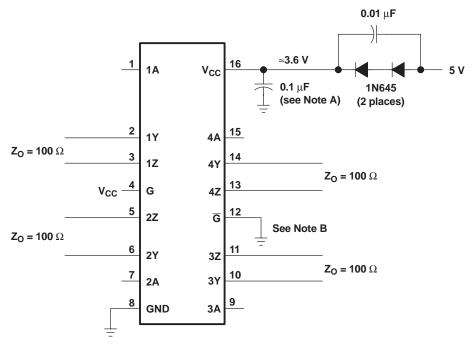
NOTES: A. Resistors are leadless, thick film (0603), 5% tolerance.

- B. Decoupling capacitance is not shown, but recommended.
- C. V_{CC} is 3 V to 3.6 V.
- D. The differential output voltage of the 'LVDS31 can exceed that specified by IEEE1394.

Figure 10. 100-Mbps IEEE 1394 Transceiver



APPLICATION INFORMATION (continued)



- A. Place a 0.1-μF Z5U ceramic, mica, or polystyrene dielectric, 0805 size, chip capacitor between V_{CC} and the ground plane. The capacitor should be located as close as possible to the device terminals.
- B. Unused enable inputs should be tied to V_{CC} or GND, as appropriate.

Figure 11. Operation With 5-V Supply

COLD SPARING

Systems using cold sparing have a redundant device electrically connected without power supplied. To support this configuration, the spare must present a high-input impedance to the system so that it does not draw appreciable power. In cold sparing, voltage may be applied to an I/O before and during power up of a device. When the device is powered off, V_{CC} must be clamped to ground and the I/O voltages applied must be within the specified recommended operating conditions.

RELATED INFORMATION

IBIS modeling is available for this device. Contact the local TI sales office or the TI Web site at www.ti.com for more information.

For more application guidelines, see the following documents:

- Low-Voltage Differential Signaling Design Notes (SLLA014)
- Interface Circuits for TIA/EIA-644 (LVDS) (SLLA038)
- Reducing EMI With LVDS (SLLA030)
- Slew Rate Control of LVDS Circuits (SLLA034)
- Using an LVDS Receiver With RS-422 Data (SLLA031)
- Evaluating the LVDS EVM (SLLA033)





24-Jan-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
5962-9762101Q2A	ACTIVE	LCCC	FK	20	1	TBD	Call TI	Call TI	-55 to 125	5962- 9762101Q2A SNJ55 LVDS31FK	Samples
5962-9762101QEA	ACTIVE	CDIP	J	16	1	TBD	Call TI	Call TI		5962-9762101QE A SNJ55LVDS31J	Samples
5962-9762101QFA	ACTIVE	CFP	W	16	1	TBD	Call TI	Call TI	-55 to 125	5962-9762101QF A SNJ55LVDS31W	Samples
SN55LVDS31W	ACTIVE	CFP	W	16	1	TBD	A42	N / A for Pkg Type	-55 to 125	SN55LVDS31W	Samples
SN65LVDS31D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31NSR	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31NSRG4	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS31	Samples
SN65LVDS31QPWQ1	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 125		
SN65LVDS31QPWRQ1	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 125		





www.ti.com

24-Jan-2013

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
SN65LVDS3487D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS3487	Samples
SN65LVDS3487DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS3487	Samples
SN65LVDS3487DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS3487	Samples
SN65LVDS3487DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDS3487	Samples
SN65LVDS9638D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DK638	Samples
SN65LVDS9638DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DK638	Samples
SN65LVDS9638DGK	ACTIVE	VSSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	AXG	Samples
SN65LVDS9638DGKG4	ACTIVE	VSSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	AXG	Samples
SN65LVDS9638DGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	AXG	Samples
SN65LVDS9638DGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	AXG	Samples
SN65LVDS9638DGN	ACTIVE	MSOP- PowerPAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	L38	Samples
SN65LVDS9638DGNR	ACTIVE	MSOP- PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	L38	Samples
SN65LVDS9638DGNRG4	ACTIVE	MSOP- PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	L38	Samples
SN65LVDS9638DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DK638	Samples
SN65LVDS9638DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DK638	Samples
SNJ55LVDS31FK	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 9762101Q2A SNJ55 LVDS31FK	Samples
SNJ55LVDS31J	ACTIVE	CDIP	J	16	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-9762101QE A SNJ55LVDS31J	Samples

www.ti.com

PACKAGE OPTION ADDENDUM

24-.lan-2013

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
SNJ55LVDS31W	ACTIVE	CFP	W	16	1	TBD	A42	N / A for Pkg Type		5962-9762101QF A SNJ55LVDS31W	Samples
SNLVDS9638DGNG4	ACTIVE	MSOP- PowerPAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	L38	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN55LVDS31, SN65LVDS31:

Catalog: SN75LVDS31



PACKAGE OPTION ADDENDUM

24-Jan-2013

● Enhanced Product: SN65LVDS31-EP

• Space: SN55LVDS31-SP

www.ti.com

NOTE: Qualified Version Definitions:

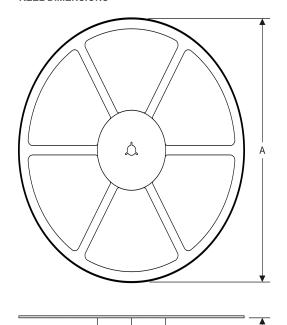
- Catalog TI's standard catalog product
- Enhanced Product Supports Defense, Aerospace and Medical Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Aug-2012

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS31DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LVDS31NSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN65LVDS31PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN65LVDS3487DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LVDS9638DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDS9638DGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDS9638DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDS9638DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 16-Aug-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS31DR	SOIC	D	16	2500	333.2	345.9	28.6
SN65LVDS31NSR	SO	NS	16	2000	367.0	367.0	38.0
SN65LVDS31PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN65LVDS3487DR	SOIC	D	16	2500	367.0	367.0	38.0
SN65LVDS9638DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
SN65LVDS9638DGNR	MSOP-PowerPAD	DGN	8	2500	358.0	335.0	35.0
SN65LVDS9638DR	SOIC	D	8	2500	340.5	338.1	20.6
SN65LVDS9638DR	SOIC	D	8	2500	367.0	367.0	35.0

14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

W (R-GDFP-F16)

CERAMIC DUAL FLATPACK



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F16 and JEDEC MO-092AC



FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



DGN (S-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com www.ti.com.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-187 variation AA-T

PowerPAD is a trademark of Texas Instruments.



DGN (S-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD $^{\text{M}}$ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206323-2/1 12/11

NOTE: All linear dimensions are in millimeters



DGN (R-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PowerPAD is a trademark of Texas Instruments



D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Communications and Telecom **Amplifiers** amplifier.ti.com www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps

DSP **Energy and Lighting** dsp.ti.com www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical logic.ti.com Logic Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

RFID www.ti-rfid.com

OMAP Applications Processors <u>www.ti.com/omap</u> TI E2E Community <u>e2e.ti.com</u>

Wireless Connectivity <u>www.ti.com/wirelessconnectivity</u>